# P6SMB11CAT3 Series, SZP6SMB11CAT3 Series

## 600 Watt Peak Power Zener Transient Voltage Suppressors

### Bidirectional*

The SMB series is designed to protect voltage sensitive components from high voltage, high energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. The SMB series is supplied in ON Semiconductor's exclusive, cost-effective, highly reliable SURMETIC® package and is ideally suited for use in communication systems, automotive, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications.

**Features**

- Working Peak Reverse Voltage Range – 9.4 to 77.8 V
- Standard Zener Breakdown Voltage Range – 11 to 91 V
- Peak Power – 600 W @ 1 ms
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- Maximum Clamp Voltage @ Peak Pulse Current
- Low Leakage < 5 μA Above 10 V
- UL 497B for Isolated Loop Circuit Protection
- Response Time is Typically < 1 ns
- AEC−Q101 Qualified and PPAP Capable
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- Pb−Free Packages are Available**

**Mechanical Characteristics:**

**CASE:** Void-Free, Transfer-Molded, Thermosetting Plastic

**FINISH:** All External Surfaces are Corrosion Resistant and Leads are Readily Solderable

**MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:** 260°C for 10 Seconds

**LEADS:** Modified L−Bend Providing More Contact Area to Bond Pads

**POLARITY:** Polarity Band Will Not be Indicated

**MOUNTING POSITION:** Any

*Please see P6SMB6.8AT3 to P6SMB200AT3 for Unidirectional devices.

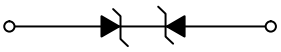
**For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**ON Semiconductor®**

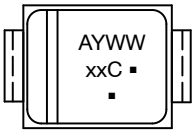
**http://onsemi.com**

**PLASTIC SURFACE MOUNT ZENER OVERVOLTAGE TRANSIENT SUPPRESSORS 9.4−78 VOLTS 600 WATT PEAK POWER**

**SMB**
**CASE 403A**
**PLASTIC**



**MARKING DIAGRAM**




xxC = Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

**ORDERING INFORMATION**

| Device | Package | Shipping† |
|---|---|---|
| P6SMBxxCAT3 | SMB | 2,500 / Tape & Reel |
| P6SMBxxCAT3G | SMB (Pb−Free) | 2,500 / Tape & Reel |
| SZP6SMBxxCAT3G | SMB (Pb−Free) | 2,500 / Tape & Reel |

The "T3" suffix refers to a 13 inch reel.

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Devices listed in ***bold, italic*** are ON Semiconductor **Preferred** devices. **Preferred** devices are recommended choices for future use and best overall value.

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## MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|---|---|---|
| Peak Power Dissipation (Note 1) @ $T_L$ = 25°C, Pulse Width = 1 ms | $P_{PK}$ | 600 | W |
| DC Power Dissipation @ $T_L$ = 75°C Measured Zero Lead Length (Note 2)<br>Derate Above 75°C<br>Thermal Resistance, Junction−to−Lead | $P_D$<br><br>$R_{\theta JL}$ | 3.0<br>40<br>25 | W<br>mW/°C<br>°C/W |
| DC Power Dissipation (Note 3) @ $T_A$ = 25°C<br>Derate Above 25°C<br>Thermal Resistance, Junction−to−Ambient | $P_D$<br><br>$R_{\theta JA}$ | 0.55<br>4.4<br>226 | W<br>mW/°C<br>°C/W |
| Operating and Storage Temperature Range | $T_J$, $T_{stg}$ | −65 to +150 | °C |

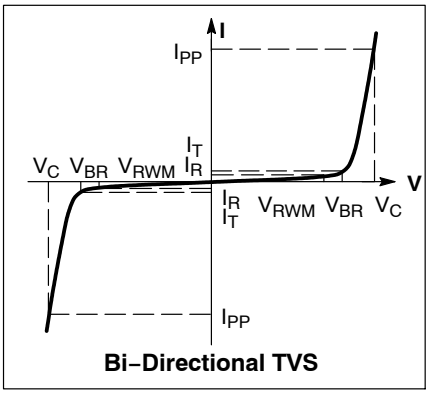
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. 10 X 1000 μs, non−repetitive
2. 1″ square copper pad, FR−4 board
3. FR−4 board, using ON Semiconductor minimum recommended footprint, as shown in 403A case outline dimensions spec.

## ELECTRICAL CHARACTERISTICS

($T_A$ = 25°C unless otherwise noted)

| Symbol | Parameter |
|---|---|
| $I_{PP}$ | Maximum Reverse Peak Pulse Current |
| $V_C$ | Clamping Voltage @ $I_{PP}$ |
| $V_{RWM}$ | Working Peak Reverse Voltage |
| $I_R$ | Maximum Reverse Leakage Current @ $V_{RWM}$ |
| $V_{BR}$ | Breakdown Voltage @ $I_T$ |
| $I_T$ | Test Current |
| $\Theta V_{BR}$ | Maximum Temperature Coefficient of $V_{BR}$ |



**Bi−Directional TVS**

## ELECTRICAL CHARACTERISTICS (Devices listed in bold, italic are ON Semiconductor Preferred devices.)

| Device* | Device Marking | $V_{RWM}$ (Note 4) | $I_R$ @ $V_{RWM}$ | Breakdown Voltage | | | | $V_C$ @ $I_{PP}$ (Note 6) | | $\Theta V_{BR}$ | $C_{typ}$ (Note 7) |
|---|---|---|---|---|---|---|---|---|---|---|---|
| | | | | $V_{BR}$ Volts (Note 5) | | | @ $I_T$ | $V_C$ | $I_{PP}$ | | |
| | | Volts | μA | Min | Nom | Max | mA | Volts | Amps | %/°C | pF |
| P6SMB11CAT3, G | 11C | 9.4 | 5 | 10.5 | 11.05 | 11.6 | 1 | 15.6 | 38 | 0.075 | 865 |
| P6SMB12CAT3, G | 12C | 10.2 | 5 | 11.4 | 12 | 12.6 | 1 | 16.7 | 36 | 0.078 | 800 |
| P6SMB13CAT3, G | 13C | 11.1 | 5 | 12.4 | 13.05 | 13.7 | 1 | 18.2 | 33 | 0.081 | 740 |
| P6SMB15CAT3, G | 15C | 12.8 | 5 | 14.3 | 15.05 | 15.8 | 1 | 21.2 | 28 | 0.084 | 645 |
| P6SMB16CAT3, G | 16C | 13.6 | 5 | 15.2 | 16 | 16.8 | 1 | 22.5 | 27 | 0.086 | 610 |
| P6SMB18CAT3, G | 18C | 15.3 | 5 | 17.1 | 18 | 18.9 | 1 | 25.2 | 24 | 0.088 | 545 |
| P6SMB20CAT3, G | 20C | 17.1 | 5 | 19 | 20 | 21 | 1 | 27.7 | 22 | 0.09 | 490 |
| P6SMB22CAT3, G | 22C | 18.8 | 5 | 20.9 | 22 | 23.1 | 1 | 30.6 | 20 | 0.09 | 450 |
| P6SMB24CAT3, G | 24C | 20.5 | 5 | 22.8 | 24 | 25.2 | 1 | 33.2 | 18 | 0.094 | 415 |
| P6SMB27CAT3, G | 27C | 23.1 | 5 | 25.7 | 27.05 | 28.4 | 1 | 37.5 | 16 | 0.096 | 370 |
| SZ/P6SMB30CAT3, G | 30C | 25.6 | 5 | 28.5 | 30 | 31.5 | 1 | 41.4 | 14.4 | 0.097 | 335 |
| ***SZ/P6SMB33CAT3, G*** | ***33C*** | ***28.2*** | ***5*** | ***31.4*** | ***33.05*** | ***34.7*** | ***1*** | ***45.7*** | ***13.2*** | ***0.098*** | ***305*** |
| SZ/P6SMB36CAT3, G | 36C | 30.8 | 5 | 34.2 | 36 | 37.8 | 1 | 49.9 | 12 | 0.099 | 280 |
| SZ/P6SMB39CAT3, G | 39C | 33.3 | 5 | 37.1 | 39.05 | 41 | 1 | 53.9 | 11.2 | 0.1 | 260 |
| SZ/P6SMB43CAT3, G | 43C | 36.8 | 5 | 40.9 | 43.05 | 45.2 | 1 | 59.3 | 10.1 | 0.101 | 240 |
| P6SMB47CAT3, G | 47C | 40.2 | 5 | 44.7 | 47.05 | 49.4 | 1 | 64.8 | 9.3 | 0.101 | 220 |
| SZ/P6SMB51CAT3, G | 51C | 43.6 | 5 | 48.5 | 51.05 | 53.6 | 1 | 70.1 | 8.6 | 0.102 | 205 |
| P6SMB56CAT3, G | 56C | 47.8 | 5 | 53.2 | 56 | 58.8 | 1 | 77 | 7.8 | 0.103 | 185 |
| SZ/P6SMB62CAT3, G | 62C | 53 | 5 | 58.9 | 62 | 65.1 | 1 | 85 | 7.1 | 0.104 | 170 |
| P6SMB68CAT3, G | 68C | 58.1 | 5 | 64.6 | 68 | 71.4 | 1 | 92 | 6.5 | 0.104 | 155 |
| P6SMB75CAT3, G | 75C | 64.1 | 5 | 71.3 | 75.05 | 78.8 | 1 | 103 | 5.8 | 0.105 | 140 |
| P6SMB82CAT3, G | 82C | 70.1 | 5 | 77.9 | 82 | 86.1 | 1 | 113 | 5.3 | 0.105 | 130 |
| P6SMB91CAT3, G | 91C | 77.8 | 5 | 86.5 | 91 | 95.5 | 1 | 125 | 4.8 | 0.106 | 120 |

4. A transient suppressor is normally selected according to the working peak reverse voltage ($V_{RWM}$), which should be equal to or greater than the DC or continuous peak operating voltage level.
5. $V_{BR}$ measured at pulse test current $I_T$ at an ambient temperature of 25°C.
6. Surge current waveform per Figure 2 and derate per Figure 3 of the General Data − 600 Watt at the beginning of this group.
7. Bias Voltage = 0 V, F = 1 MHz, $T_J$ = 25°C

*The "G" suffix indicates Pb−Free package available. Please refer back to Ordering Information on front page.

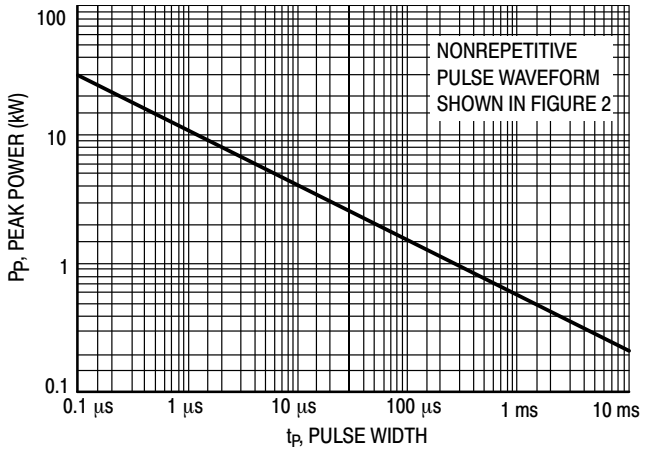



**Figure 1. Pulse Rating Curve**

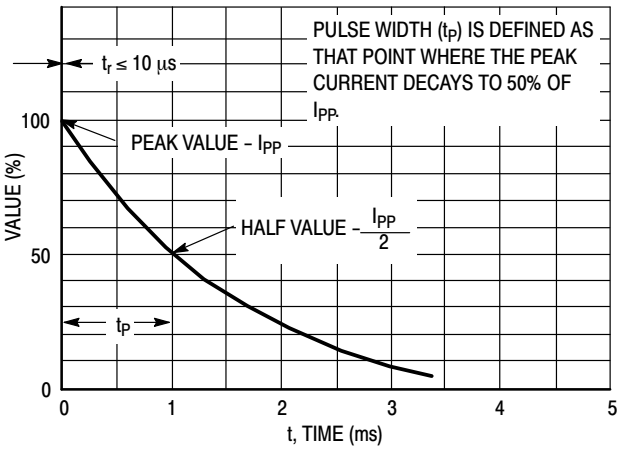



**Figure 2. Pulse Waveform**

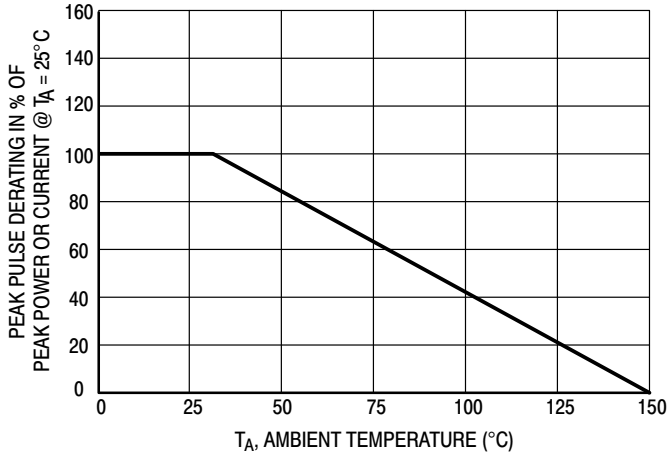



**Figure 3. Pulse Derating Curve**

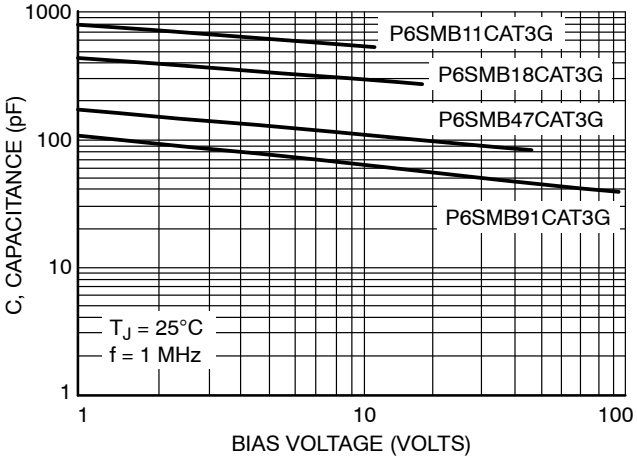
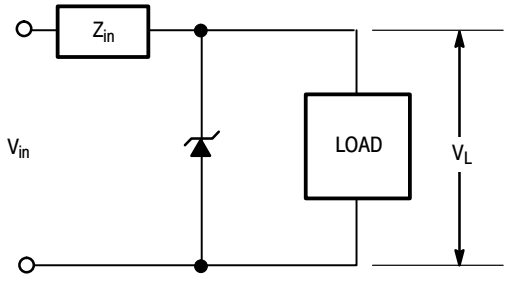



**Figure 4. Typical Junction Capacitance vs. Bias Voltage**

## TYPICAL PROTECTION CIRCUIT



## APPLICATION NOTES

### RESPONSE TIME

In most applications, the transient suppressor device is placed in parallel with the equipment or component to be protected. In this situation, there is a time delay associated with the capacitance of the device and an overshoot condition associated with the inductance of the device and the inductance of the connection method. The capacitive effect is of minor importance in the parallel protection scheme because it only produces a time delay in the transition from the operating voltage to the clamp voltage as shown in Figure 4.

The inductive effects in the device are due to actual turn-on time (time required for the device to go from zero current to full current) and lead inductance. This inductive effect produces an overshoot in the voltage across the equipment or component being protected as shown in Figure 5. Minimizing this overshoot is very important in the application, since the main purpose for adding a transient suppressor is to clamp voltage spikes. The SMB series have a very good response time, typically < 1 ns and negligible inductance. However, external inductive effects could produce unacceptable overshoot. Proper circuit layout, minimum lead lengths and placing the suppressor device as close as possible to the equipment or components to be protected will minimize this overshoot.

Some input impedance represented by $Z_{in}$ is essential to prevent overstress of the protection device. This impedance should be as high as possible, without restricting the circuit operation.

### DUTY CYCLE DERATING

The data of Figure 1 applies for non-repetitive conditions and at a lead temperature of 25°C. If the duty cycle increases, the peak power must be reduced as indicated by the curves of Figure 6. Average power must be derated as the lead or ambient temperature rises above 25°C. The average power derating curve normally given on data sheets may be normalized and used for this purpose.

At first glance the derating curves of Figure 6 appear to be in error as the 10 ms pulse has a higher derating factor than the 10 μs pulse. However, when the derating factor for a given pulse of Figure 6 is multiplied by the peak power value of Figure 1 for the same pulse, the results follow the expected trend.

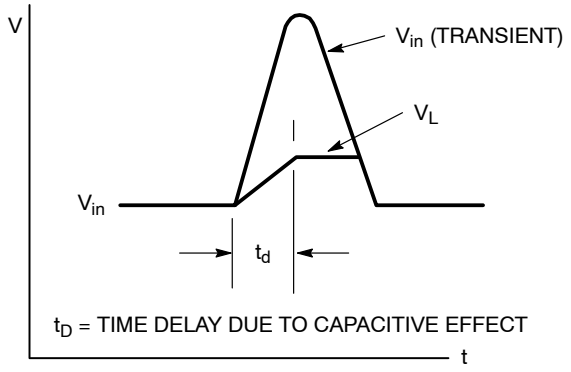



**Figure 5.**

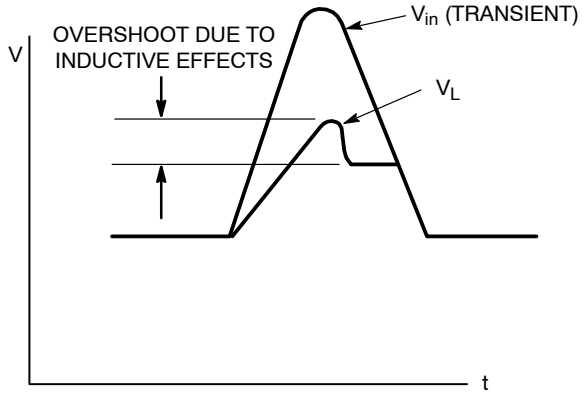



**Figure 6.**

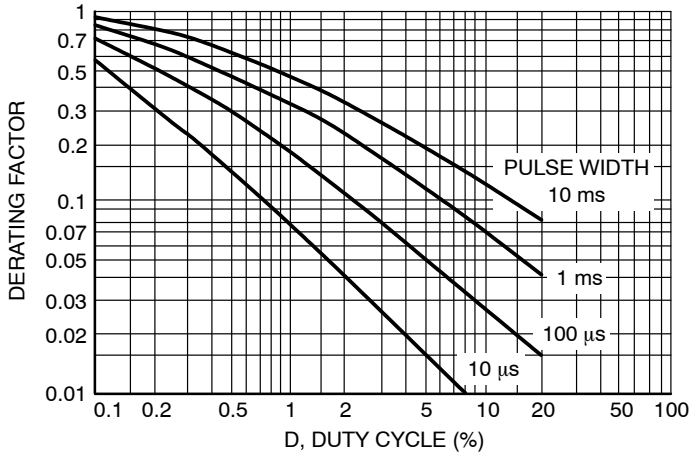



**Figure 7. Typical Derating Factor for Duty Cycle**

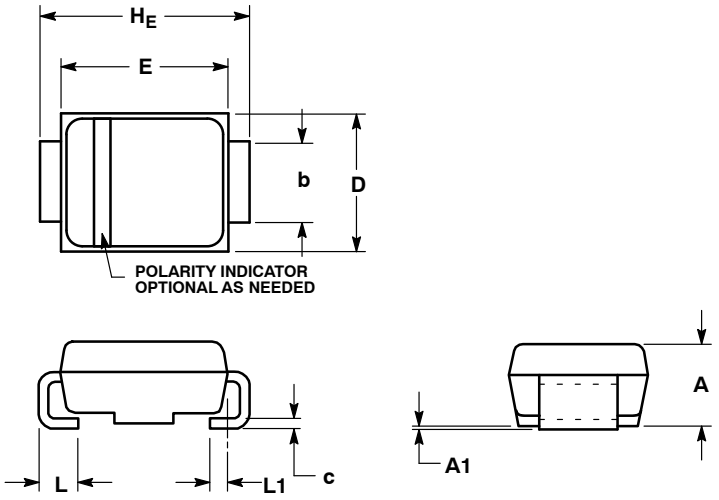
## UL RECOGNITION

The entire series has *Underwriters Laboratory Recognition* for the classification of protectors (QVGQ2) under the UL standard for safety 497B and File #E210057. Many competitors only have one or two devices recognized or have recognition in a non-protective category. Some competitors have no recognition at all. With the UL497B recognition, our parts successfully passed several tests including Strike Voltage Breakdown test, Endurance Conditioning, Temperature test, Dielectric Voltage-Withstand test, Discharge test and several more.

Whereas, some competitors have only passed a flammability test for the package material, we have been recognized for much more to be included in their Protector category.

## PACKAGE DIMENSIONS

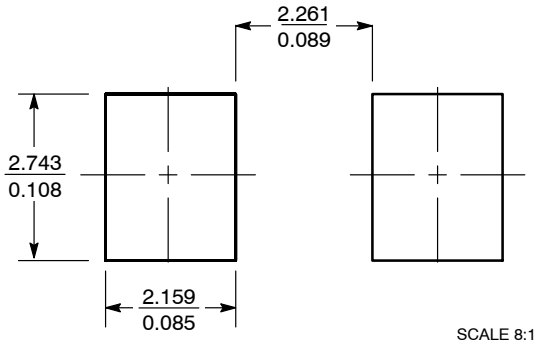
**SMB**
CASE 403A−03
ISSUE H




NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

| | MILLIMETERS | | | INCHES | | |
|---|---|---|---|---|---|---|
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 1.90 | 2.20 | 2.28 | 0.075 | 0.087 | 0.090 |
| A1 | 0.05 | 0.10 | 0.19 | 0.002 | 0.004 | 0.007 |
| b | 1.96 | 2.03 | 2.20 | 0.077 | 0.080 | 0.087 |
| c | 0.15 | 0.23 | 0.31 | 0.006 | 0.009 | 0.012 |
| D | 3.30 | 3.56 | 3.95 | 0.130 | 0.140 | 0.156 |
| E | 4.06 | 4.32 | 4.60 | 0.160 | 0.170 | 0.181 |
| $H_E$ | 5.21 | 5.44 | 5.60 | 0.205 | 0.214 | 0.220 |
| L | 0.76 | 1.02 | 1.60 | 0.030 | 0.040 | 0.063 |
| L1 | 0.51 REF | | | 0.020 REF | | |

## SOLDERING FOOTPRINT*




*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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**P6SMB11CAT3/D**